1. Product Features

1.1 Electrical features

- V_{CES}=1200V
- $I_{C\ nom}$=200A / I_{CRM}=400A
- Low switching losses
- Low inductance
- Fast switching and short tail current
- Integrated NTC temperature sensor
- High power and thermal cycling capability

Figure 1 IGBT Module

1.2 Mechanical features

- Si_3N_4 substrate with low thermal resistance
- Copper base plate

2. Typical Applications

- Automotive application
- Hybrid and electric vehicle
- Inverter for motor drive

3. Description

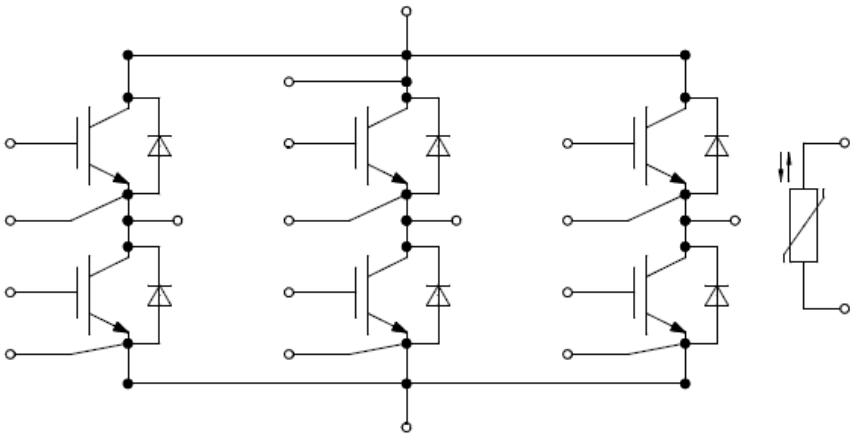


Figure 2 3 Phase Bridge

4. IGBT

4.1 Maximum rated values

Parameter	Note or test condition	Symbol	Values	Unit
Collector-emitter voltage 集电极—发射极间电压	T_{vj} = 25°C	V_{CES}	1200	V
Continuous DC collector current 连续集电极电流	T_C = 85°C, $T_{vj\ max}$ = 150°C	$I_{C\ nom}$	200	A
Repetitive peak collector current 集电极峰值电流	t_P = 1 ms	I_{CRM}	400	A
Total power dissipation 总功率损耗	T_C = 25°C, $T_{vj\ max}$ = 175°C	P_{tot}	880	W
Gate-emitter peak voltage 栅极－发射极峰值电压		V_{GES}	+/- 20	V

4.2 Characteristic value

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage 集电极－发射极饱和电压	I_C = 200 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE,sat}$		1.59 1.86 1.94		V V V
Gate threshold voltage 栅极阈值电压	I_C = 6mA, V_{CE} = V_{GE}, T_{vj} = 25°C		$V_{GE,th}$	5.0	5.8	6.5	V
Gate charge 栅极电荷	V_{GE} = -15 V ... +15 V		Q_G		1.90		µC
Internal gate resistor 内部栅极电阻	T_{vj} = 25°C		R_{Gint}		1.70		Ω
Input capacitance 输入电容	f=1MHz, T_{vj}=25°C, V_{CE}=25V, V_{GE}=0V		C_{ies}		33.4		nF
Reverse transfer capacitance 反向传输电容	f=1MHz, T_{vj}=25°C, V_{CE}=25V, V_{GE}=0V		C_{res}		0.17		nF
Collector-emitter cut-off current 集电极-发射极截止电流	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1	mA
Gate-emitter leakage current 栅极-发射极漏电流	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
Turn-on delay time, inductive load 开通延迟时间	I_C = 200A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,on}$ = 2.2Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d,on}$		0.12 0.14 0.15		us us us
Rise time, inductive load 上升时间	I_C = 200A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,on}$ = 2.2Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0.04 0.05 0.05		us us us

(table continues...) 待续

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time, inductive load 关断延迟时间	I_C = 200A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,off}$ = 2.2Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d,off}$		0.26 0.30 0.31		us us us
Fall time, inductive load 下降时间	I_C = 200A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,off}$ = 2.2Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0.22 0.31 0.33		us us us
Turn-on energy loss per pulse 开通损耗能量	I_C = 200A, V_{CE} = 600V, L_s=30nH V_{GE} = +15/-15V, di/dt =3200A/μs $R_{G,on}$ = 2.2Ω (T_{vj} = 150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		10.3 17.3 18.4		mJ mJ mJ
Turn-off energy loss per pulse 关断损耗能量	I_C = 200A, V_{CE} = 600V, L_s=30nH V_{GE} = +15/-15V, dv/dt =5610V/μs $R_{G,off}$ = 2.2Ω (T_{vj} = 150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		14.3 20.5 21.7		mJ mJ mJ
SC data 短路数据	V_{GE} ≤15V, V_{CC} =600 V, t_P ≤ 8 μs, T_{vj} = 150°C , C_{GE} = 0.0uF , V_{CEmax} = V_{CES} - L_{sCE} · di/dt		I_{SC}		1407		A
Thermal resistance, junction to case 结一外壳热阻	Per IGBT		$R_{th,JC}$			0.17	K/W

5. Diode

5.1 Maximum rated values

Parameter	Note or test condition	Symbol	Values	Unit
Repetitive peak reverse voltage 反向重复峰值电压	T_{vj} = 25°C	V_{RRM}	1200	V
Continuous DC forward current 连续正向直流电流		I_F	200	A
Repetitive peak forward current 正向重复峰值电流	t_P = 1 ms	I_{FRM}	400	A

5.2 Characteristic value

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Forward voltage 正向电压	I_F = 200 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1.73 1.60 1.55		V V V

(table continues...) 待续

由 Foxit PDF Editor 编辑
版权所有 (c) by Foxit 公司, 2003 - 2010
仅用于评估。

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Peak reverse recovery current 反向恢复峰值电流	I_F = 200A, V_R = 600V V_{GE} = -15V , - di_F/dt = 1240 A/µs (T_{vj}=150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		221 261 276		A A A
Recovered charge 恢复电荷	I_F = 200A, V_R = 600V V_{GE} = -15V , - di_F/dt = 1240 A/µs (T_{vj}=150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		22.5 43.1 49.2		µC µC µC
Reverse recovery energy 反向恢复损耗（每脉冲）	I_F = 200A, V_R = 600V V_{GE} = -15V , - di_F/dt = 1240 A/µs (T_{vj}=150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		8.63 17.9 20.8		mJ mJ mJ
Thermal resistance, junction to case 结－外壳热阻	Per diode		$R_{th,JC}$			0.22	K/W

6. NTC-Thermistor

6.1 Characteristic value

Parameter	Note or test condition	Symbol	Values			Unit
			Min.	Typ.	Max.	
Rated resistance 额定电阻值	Tc = 25°C	R_{25}		5.00		KΩ
Power dissipation 耗散功耗	Tc = 25°C	P_{25}			20	mW
B-value B-Z 值	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298, 15K))]$	B_{25}/B_{50}		3375		K
B-value B-Z 值	$R_2=R_{25}\exp[B_{25/75}(1/T_2-1/(298, 15K))]$	B_{25}/B_{75}		3408		K
B-value B-Z 值	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298, 15K))]$	B_{25}/B_{100}		3436		K

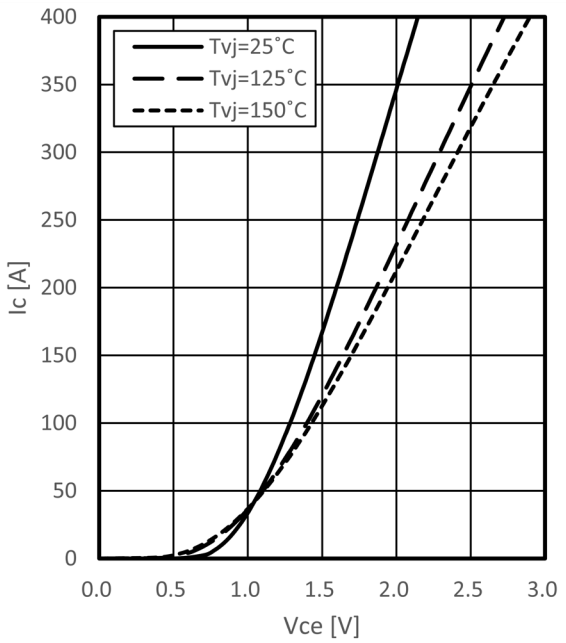
Technical datasheet

7. Module

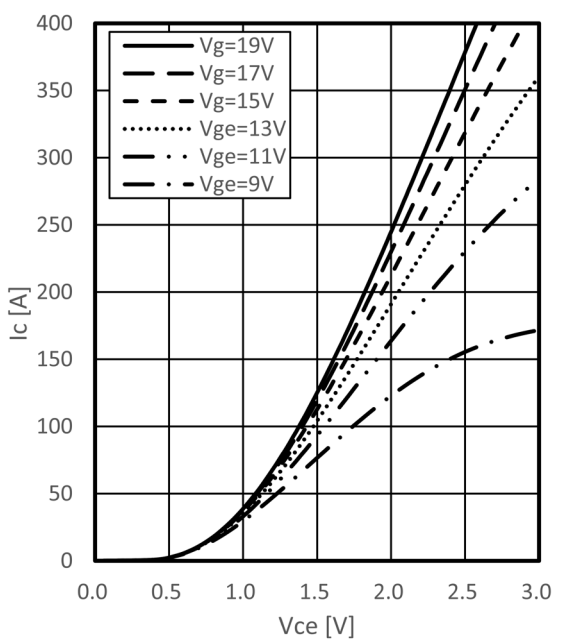
7.1 Characteristic value

Parameter	Note or test condition	Symbol	Values			Unit
			Min.	Typ.	Max.	
Isolation Voltage 隔离电压	RMS, f=50HZ,1min	V_{ISOL}			2500	V
Stray inductance module 杂散电感		L_{sCE}		20		nH
Operation Junction Temperature 结温		T_{jop}	-40		150	˚C
Storage Temperature Range 存储温度范围		T_{stg}	-40		125	˚C
Mounting Torque 安装扭矩	Screw M5	M	3.0		6.0	N.m
Terminal Connection Torque 端子扭矩	Screw M6	M	3.0		6.0	N.m
Weight of Module 重量		G		400		g

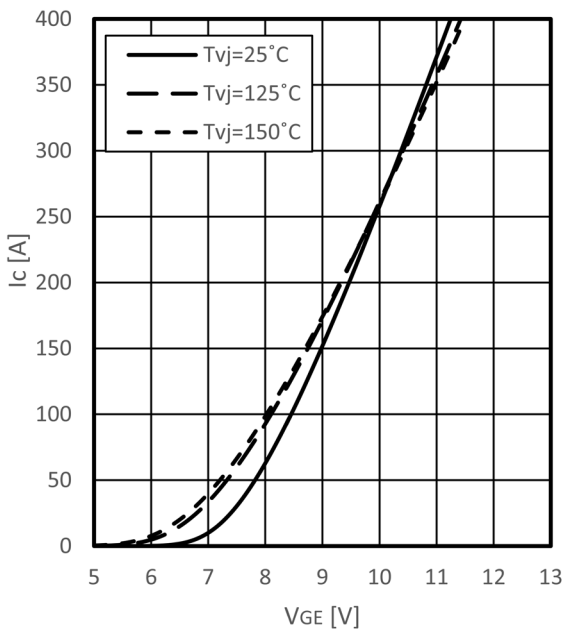
8. Characteristics diagrams



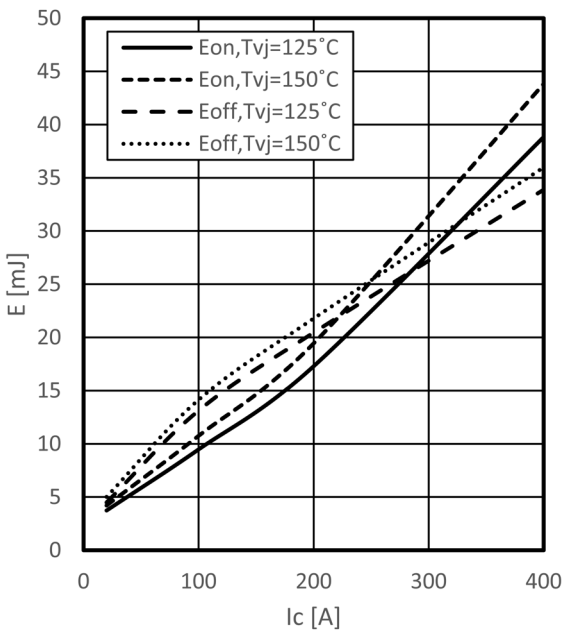
Output characteristic IGBT (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15V$



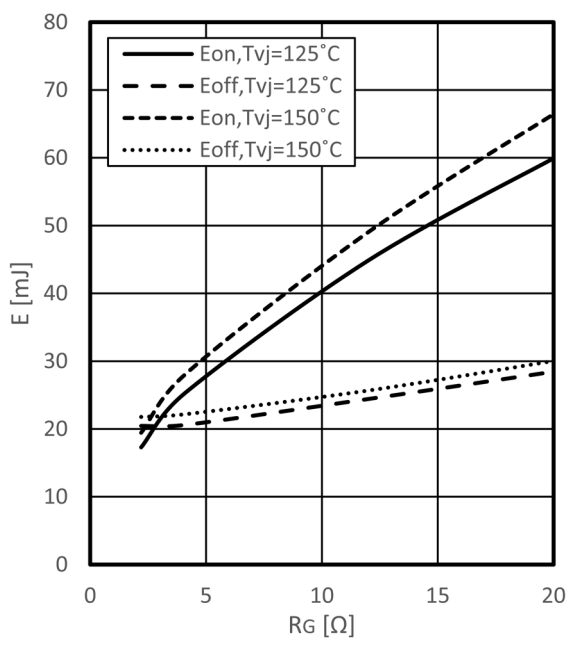
Output characteristic IGBT (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150°C$



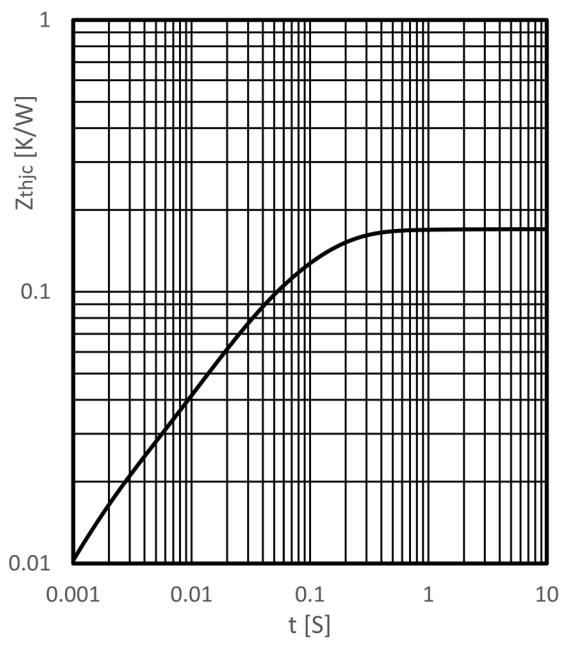
Transfer characteristic IGBT (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20V$



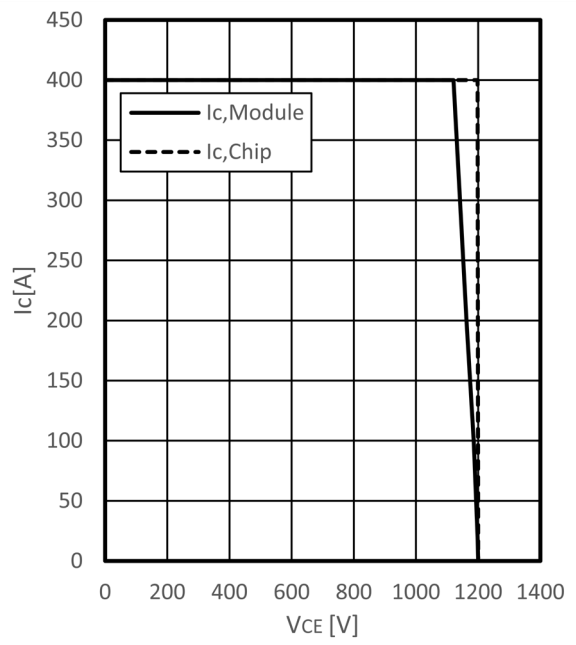
Switching losses IGBT (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$R_{Goff} = 2.2\ \Omega$, $R_{Gon} = 2.2\ \Omega$, $V_{CE} = 600\ V$, $V_{GE} = \pm 15\ V$



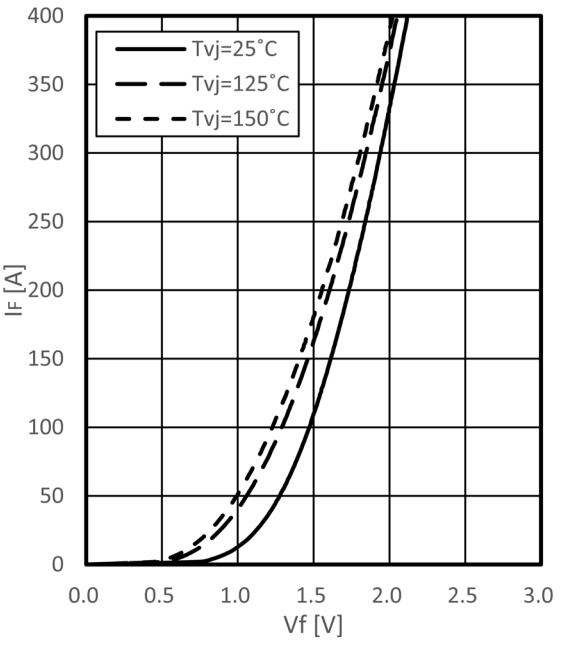
Switching losses IGBT (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$I_C = 200$ A, $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V



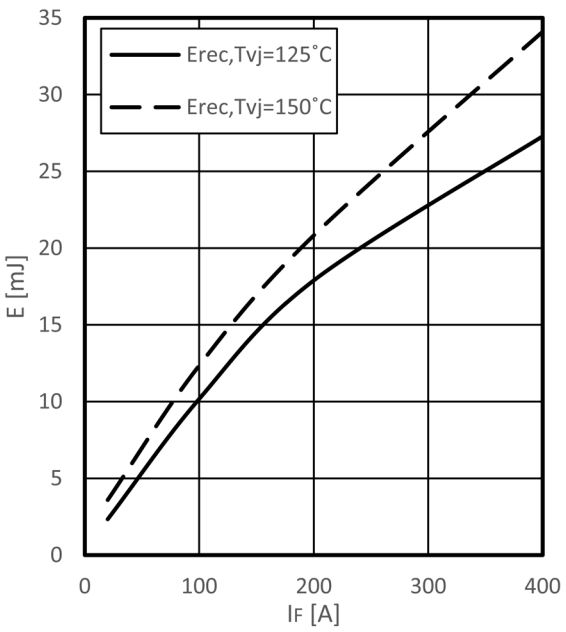
Transient thermal impedance IGBT
$Z_{thJC} = f(t)$



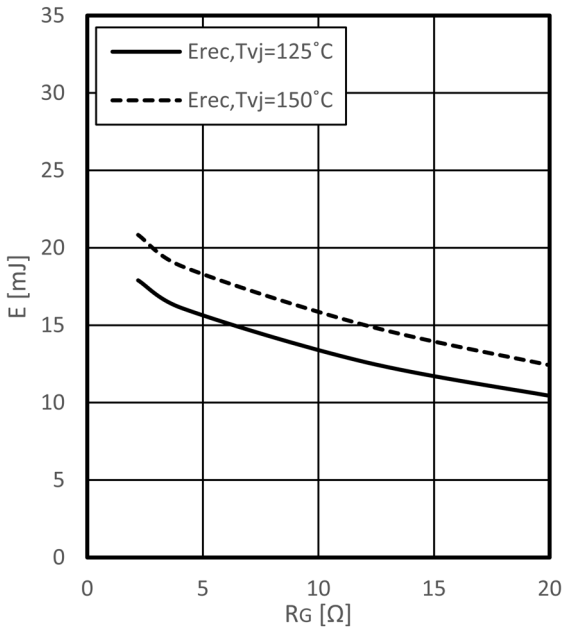
Reverse bias safe operating area IGBT (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V, $R_{Goff} = 2.2\ \Omega$, $T_{vj} = 150$ °C



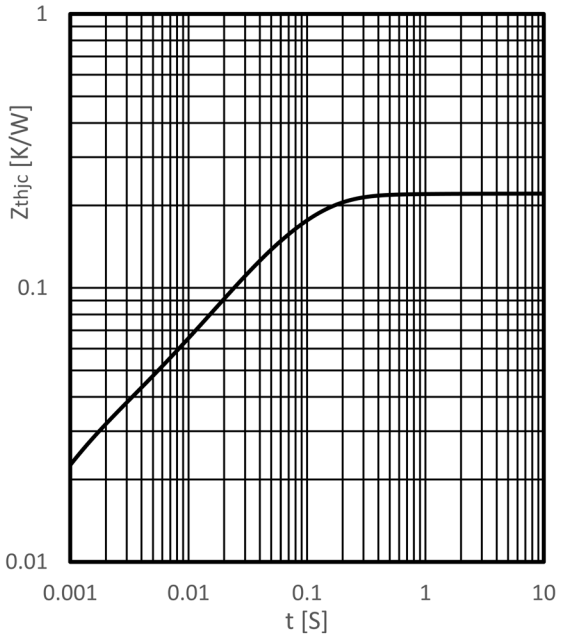
Forward characteristic of Diode (typical)
$I_F = f(V_F)$



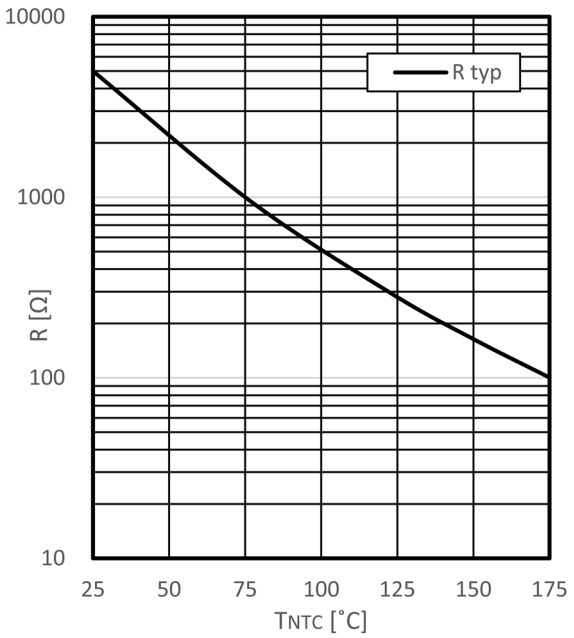
Switching losses Diode (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 2.2\ \Omega$, $V_{CE} = 600$ V



Switching losses Diode (typical)
$E_{rec} = f(R_G)$
$I_F = 200$ A, $V_{CE} = 600$ V



Transient thermal impedance Diode
$Z_{thJC} = f(t)$



NTC-Thermistor-temperature characteristic (typical)
$R = f(T_{NTC})$

9. Circuit Diagram

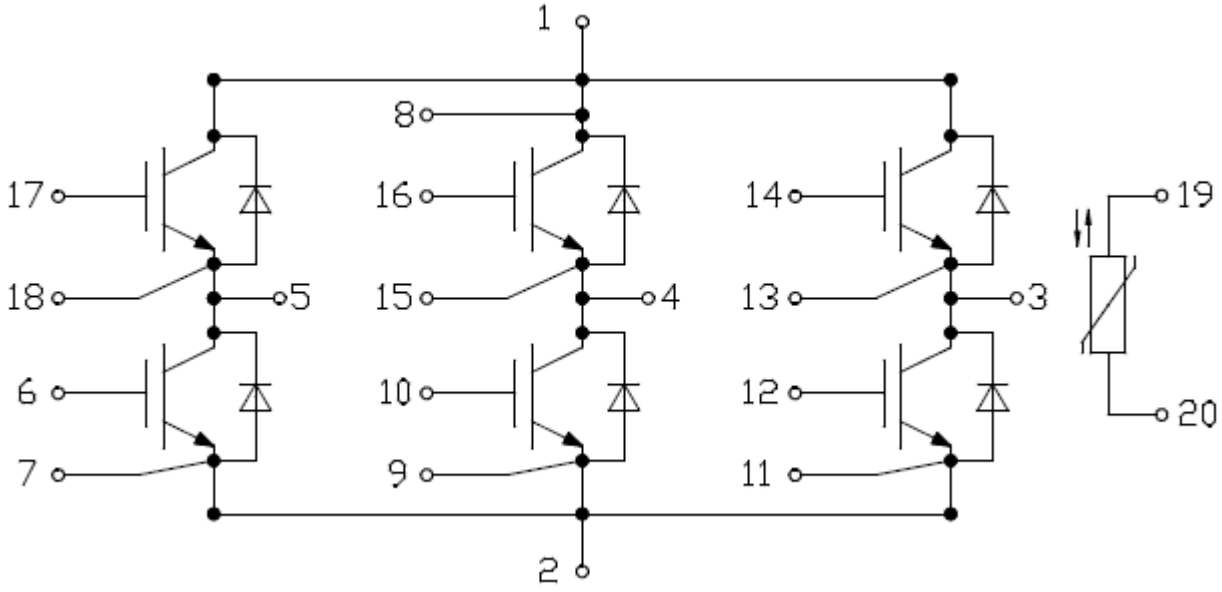


Figure 3

10. Package Outlines

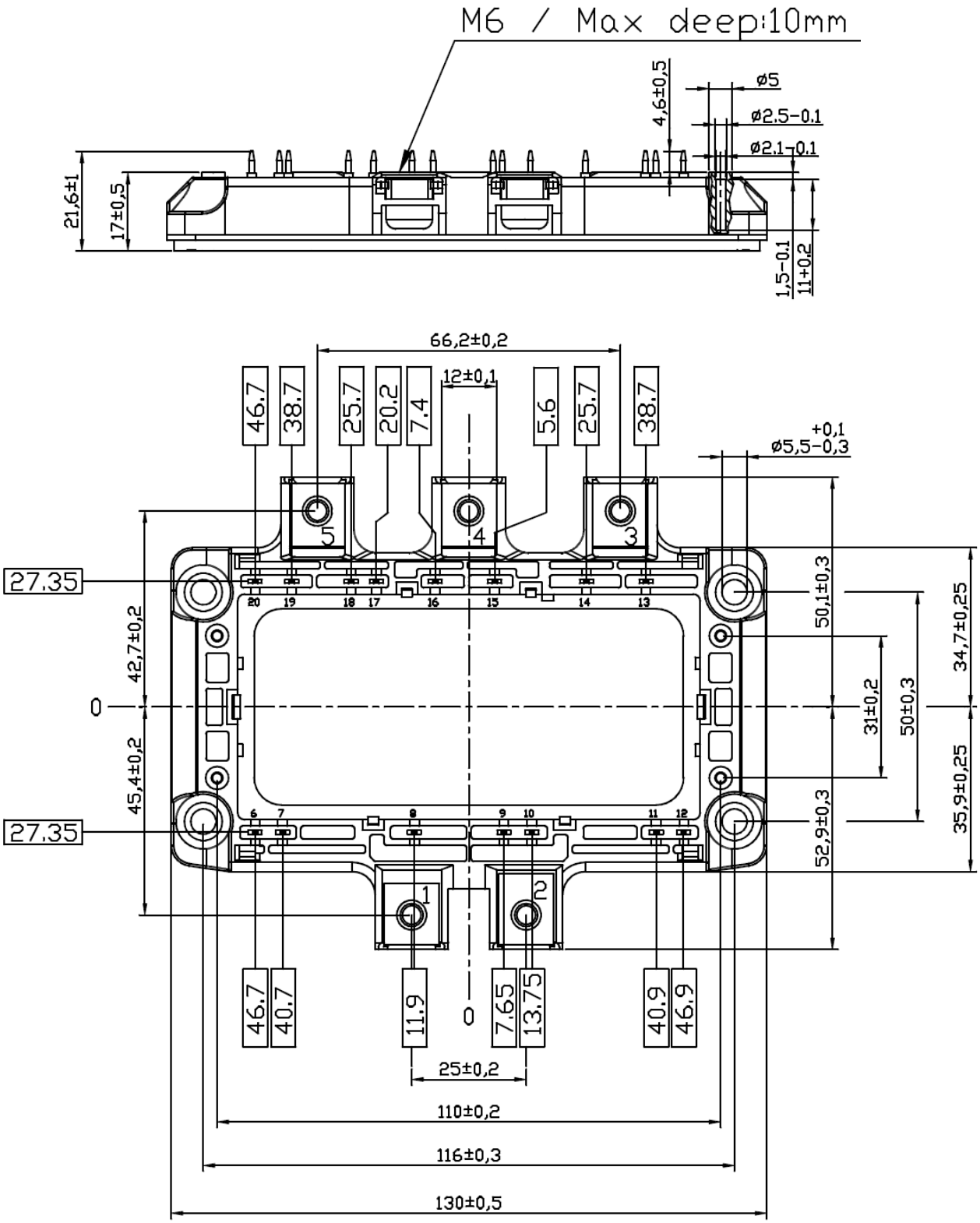


Figure 4